



TECHNICAL UNIVERSITY OF MOMBASA

SCHOOL OF ENGINEERING AND TECHNOLOGY

DEPARTMENT OF MEDICAL ENGINEERING

UNIVERSITY EXAMINATION FOR:

BACHELOR OF SCIENCE IN MEDICAL ENGINEERING

ECL 4404: MEDICAL OPTICS II.

SPECIAL/ SUPPLEMENTARY EXAMINATION

SERIES: JULY, 2025

TIME: 2 HOURS

DATE: JULY, 2025

Instructions to Candidates

You should have the following for this examination

-Answer Booklet, examination pass and student ID

This paper consists of FIVE questions. Answer question ONE and any other TWO

Do not write on the question paper.

Question ONE

- (a) Discuss the essential requirements for the construction of a laser. (10 marks)
- (b) A 3mW laser beam of wavelength $\lambda = 6 \times 10^{-5}$ is focused by a convex lens. The focal length of the lens is 5 cm and radius of the circular aperture is 1 cm.
- (i) Find the intensity of the focused spot.
- (ii) If the coherence time of the laser is 50ns, find the monochromaticity of the source. (7 marks)
- (c) Describe qualitatively how a He-Ne laser works. (13 marks)

Question TWO

- (a) Distinguish between temporal and spatial coherence. (3 marks)
- (b) Describe metastable states. Give examples (3 marks)
- (c) Calculate the gain constant α_{12} of a laser beam from the following data N_2 . $N_1 = 5 \times 10^{16} \text{ cm}^{-3}$, $\lambda_0 = 65000 \text{ \AA}$, line-width $\lambda = 15 \text{ \AA}$ and the lifetime for spontaneous emission $= 2 \times 10^{-4} \text{ s}$ (7 marks)
- (d) Using an energy level diagram describe the principle of operation of Nd:YAG laser. (7 marks)

Question THREE

- (a) Describe qualitatively of operation of carbon diode laser with the aid of energy band diagrams. (15 marks)
- (b) Calculate the ratio of stimulated to spontaneous emission rate at a temperature of 250° for sodium D lines. (5 marks)

Question FOUR

- (a) Explain the concept of negative temperature in connection with the operation of a laser. (3 marks)
- (b) (i) By considering the rate equations for a three level laser, derive an expression for the threshold population inversion in terms of the laser parameters. Hence compare the pump power required to bring a three level and four level laser to threshold.
- (ii) Calculate the threshold pumping power for an Nd: glass laser, given that the critical population inversion is $9 \times 10^{21} \text{ m}^{-3}$, the spontaneous lifetime is 300 μs and that the upper laser level is at an energy of 1.4 eV. (10 marks)
- (c) Discuss the application of lasers in medical field. (5 marks)
- (d) Explain high monochromacity and high directionality of laser radiation. (2 marks)

Question FIVE

- (a) Compare the ideal light output against current characteristics for the injection laser with one from a more typical device. Discuss the major points on the characteristics and indicate why the two differ. (5marks)
- (b) For 2p-----1s transition in hydrogen atom, the mean spontaneous lifetime is $1.66 \times 10^{-8} \text{ sec.}$ and the frequency of emitted radiation is $2.4 \times 10^{15} \text{ Hz.}$ Calculate the probability of stimulated emission (3.5 marks)
- (c) With the help of energy level diagrams discuss the liquid dye lasers. (11.5 marks)

PHYSICAL CONSTANTS

Permittivity of free space	$8.854 \times 10^{-12} \text{ F/M}$
Permeability of free space	$4\pi \times 10^{-7} \text{ H/M}$
Electron charge	$1.602 \times 10^{-19} \text{ C}$
Electron rest mass	$9.108 \times 10^{-31} \text{ kg}$
Electron charge/mass ratio	$1.759 \times 10^{11} \text{ C/kg}$
Photon rest mass	1836m
Planck's constant	$6.625 \times 10^{-34} \text{ Js}$
Boltzmann's constant	$1.38 \times 10^{-23} \text{ J/K}$
Speed of light	$3 \times 10^8 \text{ ms}^{-1}$
kT at room temperature	0.0259 eV

Properties of some common semiconductors at room temperature (300K)

	Silicon	Germanium
Relative permittivity, ϵ_r	11.8	16
Energy gap, E eV	1.08	0.66
Electron mobility, $\mu_e \text{ m}^2/\text{Vs}$	0.13	0.38
Hole mobility, $\mu_h \text{ m}^2/\text{Vs}$	0.05	0.18
Intrinsic concentration, $n_i \text{ m}^{-3}$	1.4×10^{16}	2.5×10^{19}
Density of state at CB, $N_c \text{ m}^{-3}$	2.8×10^{25}	1×10^{25}
Density of state at VB, $N_v \text{ m}^{-3}$	1×10^{25}	1.4×10^{24}
Effective electron mass, m_c^*	1.1m	0.55m
Effective hole mass, m_h^*	0.56m	0.37m